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November 2013

FQPF9P25

P-Channel QFET® MOSFET

-250 V, -6 A, 620 mΩ

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Toted DC motor control, and variable switching power applications.

Features

- -6 A, -250 V, $R_{DS(on)}$ = 620 m Ω (Max.) @ V_{GS} = -10 V, $I_{D} = -3 A$
- · Low Gate Charge (Typ. 29 nC)
- · Low Crss (Typ. 27 pF)





Absolute Max num Tatings To = 20 C unless c howese noted

Symbo!	Parameter	FQPF9P25	Unit
V _{DS}	ain ource Voltage	-250	V
	Continuous (T _i) = 25°C)	-6.0	Α
	- Continuous (T _C = 100°C)	-3.9	Α
I _{DM}	Drain Current Pulsod (Note 1)	-24	Α
7	Ga'e-Source /ultage	± 30	V
LAS	Single Pusch Avalenche Energy (Note 2)	650	mJ
I _N R	Avalanche Curren: (Note 1)	-6.0	Α
EAR	Repetitive Avalariche Energy (Note 1)	5.0	mJ
dv/dt	Peak Dic 1e Recovery dv/dt (Note 3)	-5.5	V/ns
P _D	Power Dissipation (T _C = 25°C)	50	W
- Derate above 25°C		0.4	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.	300	°C

Thermal Characteristics

Symbol	Parameter	FQPF9P25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF9P25	FQPF9P25	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-250			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.2		V/°C
I _{DSS}	Zoro Cata Valtago Drain Current	V _{DS} = -250 V, V _{GS} = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = -200 V, T _C = 125°C			2	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -30 V, V _{DS} = 0 V			-10	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V		(F-)	10r	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0	5 C	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_D = -3.\iota$		0.45 ป.62	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -40^{\circ} /, I_{D}$		4.8	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 5 \text{ V, } V_{GS} = 0 \text{ V,}$ = - $510 11 20 $	pF
Coss	Output Capacitance	= 1.0 N. 2	pF
C _{rss}	Reverse Transfer Capacitance	27 35	pF

Switching Characteristi 3

t _{d(on)}	Turn-On D , me $v_{DD} = -125$ v, $l_D = -9.4$ A,	 20	50	ns
t _r	Turn-On se Time $R_G = 2.7.2$	 150	310	ns
t _{d(off)}) Off L ay Tim	 45	100	ns
t _f	Furn ConFall (Note 4)	 65	140	ns
Q_g	rotal Ga Charge $V_{DS} = -200 \text{ V, } I_D = -9.4 \text{ A,}$	 29	38	nC
	Ge surce Charge V _{GS} = -10 V	 7.6		nC
\overline{Q}_{gd}	ate-Drain Charge (Note 4)	 14		nC

rce Diode Characteristics and Maximum Ratings

alli G	ani o vii de Biode o vardoistic tivo dila maximani ratingo						
Is	Maximum Continuous Orain-Source Diode Forward Current				-6.0	Α	
'Sit1	Maximum Pulsed Drain-Source Diode Forward Current			-	-24	Α	
'SD	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -6.0 \text{ A}$		-	-5.0	٧	
t _{rr}	Reverse Fleudvery Time	$V_{GS} = 0 \text{ V, } I_{S} = -9.4 \text{ A,}$		190		ns	
Q _{rr}	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		1.45	/	μС	

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 28.9 mH, I $_{AS}$ = -6.0 A, V $_{DD}$ = -50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3. I $_{SD}$ ≤ -9.4 A, di/dt ≤ 300 A/ μ s , V $_{DD}$ = BV $_{DSS}$, starting T $_{J}$ = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

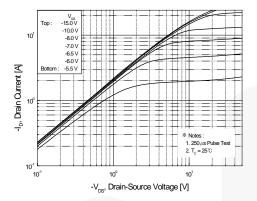


Figure 1. On-Region Characteristics

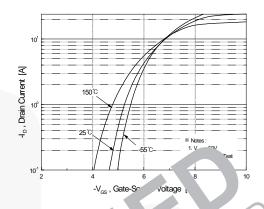
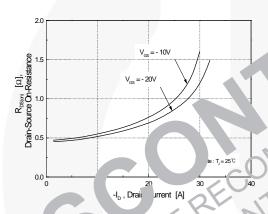


Figure 2. \ nst Char .eristics



Draid Surrent and Gate Voltage

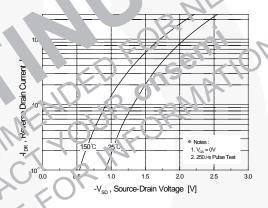


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

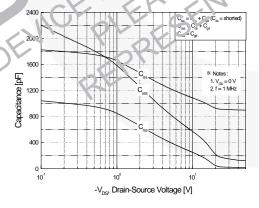


Figure 5. Capacitance Characteristics

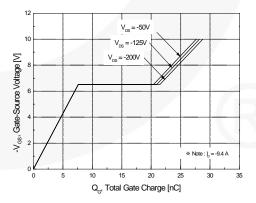


Figure 6. Gate Charge Characteristics

1.2 (Normalized) 1.0 (Normalized) 1.0 (Normalized) 1.0 (Normalized) 1.0 (Normalized) 1.0 (Normalized) 1.0 (Normalized) 2.0 (Normalized) 2.0 (Normalized) 2.0 (Normalized)

Typical Characteristics (Continued)

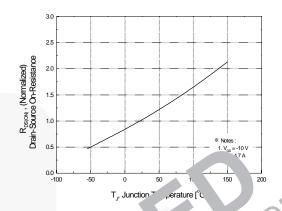
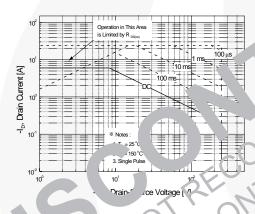


Figure 7. Breakdown Voltage Variation vs. Temperature

 T_J , Junction Temperature [°C]

150

Figure 8. C. Re. (ance ariation vs. mp. .e



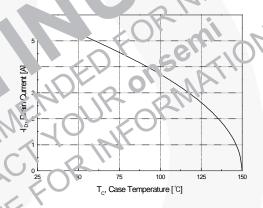


Figure 9. / iximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

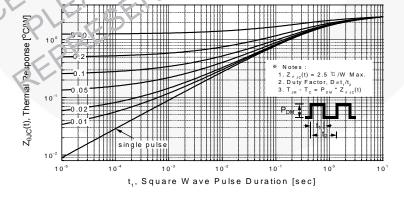


Figure 11. Transient Thermal Response Curve

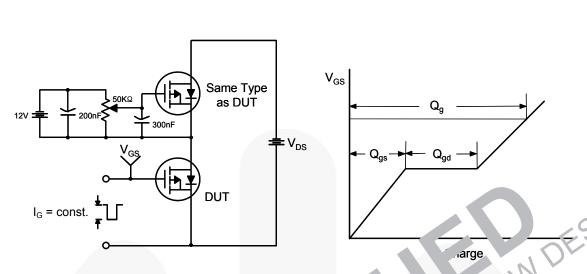


Figure 12. Gate Charge Test Circuit & Vave. m

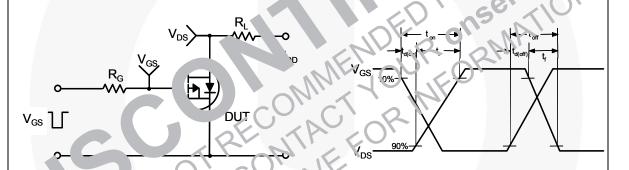


Figure 13. Resistive Switching Test Circuit & Waveforms

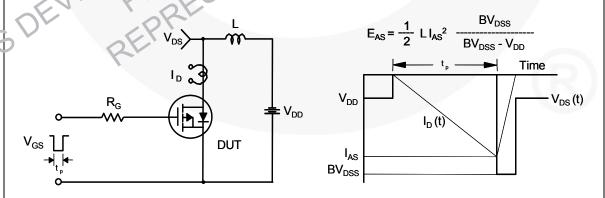
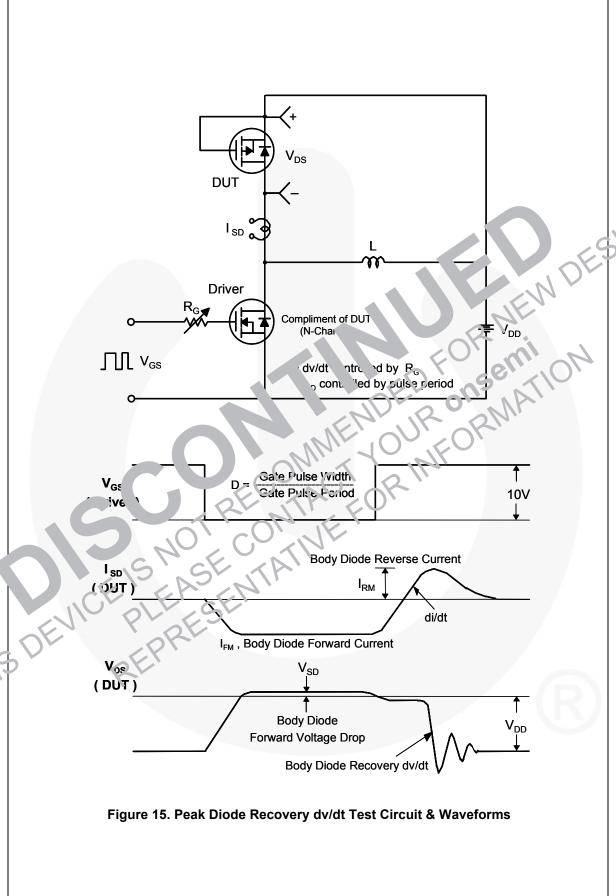


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions 10.36 Α 9.96 Ø^{3.28} 7.00 3.08 3.40 (0.70)3.20 SEE NOTE "F" SEE NOTE "F" 6.88 6.48 1 X 45° 16 16.00 15.60 2.14 O 10.05 9.45 0.45 NOTES: A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A. B DOES NOT COMPLY EIAJ STD. VALUE. ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONS ARE EXCLUSIVE OF BURRS 4.90 /B/ 4.50 MOLD FLASH AND TIE BAR PROTRUSIÓNS. E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994. OPTION 1 - WITH SUPPORT PIN HOLE. OPTION 2 - NO SUPPORT PIN HOLE. G. DRAWING FILE NAME: TO220M03REV3

Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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